

**REMARKS**

The amendment to the claims is supported by the specification at page 8, line 16 to page 10, line 7. Applicants submit that the amendment does not add any new matter to the disclosure.

The invention centers on silicon-containing resist compositions wherein a high silicon content can be achieved through use of silicon-containing additives which are free of acid labile moieties and/or which contain lactone. The compositions of the invention enable high silicon content to be achieved without excessive silicon on the resist polymer where such silicon may undesirably alter performance.

Hasegawa et al. (US 2002/0061465 A1) discloses acid-labile silicon-containing additives for use as dissolution inhibitors in combination with specific silicon-containing polymers. Hasegawa et al. does not disclose or suggest resist compositions containing silicon-containing additives which are free of acid labile moieties and/or which contain lactone. Applicants submit that the presently claimed additives would either not actively affect the solubility of the resist or would act to promote the solubility of the resist. See the specification at page 8, line 16-21.

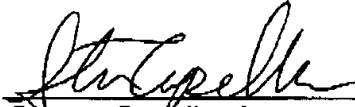
Lin (US 5304453) is cited as showing the equivalence of oxygen plasma etching and reactive ion etching. Applicants concede the use of a specific etching method would generally be a matter of choice. Nevertheless, applicants submit that the combination of Hasegawa et al. and Lin would still fail to suggest the claimed resist compositions which contain silicon-containing additives which are free of acid labile moieties and/or which contain lactone.

For the above reasons, applicants submit that the application is now in condition for allowance. Such allowance is earnestly and respectfully solicited.

Respectfully submitted,

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